

In the Claims

Please replace all prior versions of claims in the application with the following list of claims:

X. (Currently amended) A method for forming in monolithic form a DRAM-type memory, including the steps of:

forming, on a single-crystal semiconductor substrate, parallel strips including a lower insulating layer, a strongly-conductive layer, a single-crystal semiconductor layer, and an upper insulating layer;

forming, perpendicularly to the parallel strips, in the upper insulating layer and in at least a portion of the single-crystal semiconductor layer, first and second parallel trenches, each of the first and second parallel trenches being shared by neighboring cells;

forming, in each of the first parallel trenches, a first conductive line according to a strip width;

B forming, in each of the second parallel trenches, a pair of second distinct parallel conductive lines, insulated from the layers peripheral to the second ^{*parallel*} trench;

filling the first and second parallel trenches with an insulating material;

removing the remaining portions of the upper insulating layer; and

depositing a conductive layer,

B wherein the first and second parallel trenches are formed in the upper insulating layer and at least a portion of the single-crystal semiconductor layer so that the first parallel trenches have a minimum width, and the second parallel trenches have a width which is twice that of the first parallel trenches, two neighboring parallel trenches being separated by a minimum interval, each first trench being surrounded with two second ^{*parallel*} parallel trenches and each second trench being surrounded with two first ^{*parallel*} parallel trenches.

2. (Currently amended) The method of claim 1, wherein the forming of the parallel strips includes the steps of:

forming on a first single-crystal semiconductor substrate a single-crystal semiconductor layer resting on a first insulating layer;